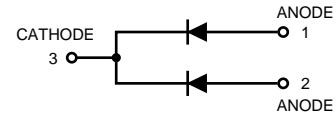
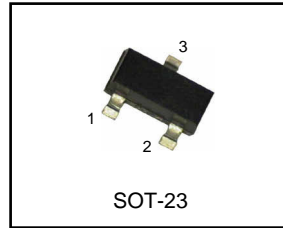


Monolithic Dual Switching Diode

MMBD6100



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	VR	70	Vdc
Peak Forward Current	IF	200	mAdc
Peak Forward Surge Current	IFM(surge)	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max.	Unit
Total Device Dissipation FR-5 Board ⁽¹⁾ TA=25°C Derate above 25°C	PD	225 1.8	mW mW / °C
Thermal Resistance, Junction to Ambient	R θ JA	556	°C / W
Total Device Dissipation Alumina Substrate, ⁽²⁾ TA=25°C Derate above 25°C	PD	300 2.4	mW mW / °C
Thermal Resistance, Junction to Ambient	R θ JA	417	°C / W
Junction and Storage Temperature	TJ,TSTG	-55 to +150	°C

DEVICE MARKING

MMBD6100=5BM

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min.	Max.	Unit
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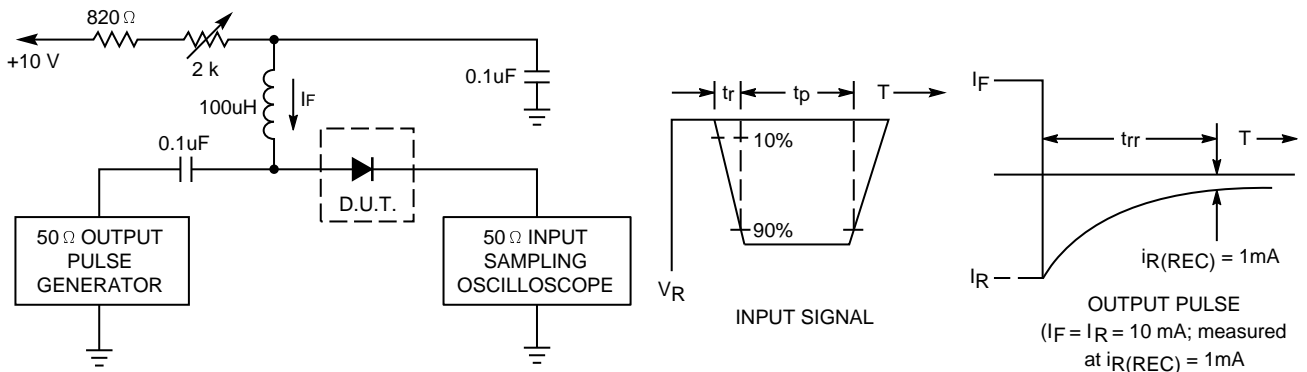
OFF CHARACTERISTICS

Reverse Breakdown Voltage (IBR=100uAdc)	V(BR)	70	-	Vdc
Forward Voltage (IF=1.0 mAdc) (IF=100 mAdc)	VF	550 850	700 1100	mVdc
Reverse Voltage Leakage Current (VR=50 Vdc)	IR	- -	0.1	uAdc
Diode Capacitance (VR=0, f=1.0MHZ)	CJ	-	2.5	pF
Reverse Recovery Time (IF=IR=10 mAdc, IR(REC)=1.0mAdc)	trr	-	4.0	nS

(1) FR-5=1.0 x 0.75 x 0.062in.

(2) Alumina=0.4 x 0.3 x 0.024in. 99.5% alumina.

FIGURE 1. RECOVERY TIME EQUIVALENT TEST CIRCUIT



- Notes: 1. A 2.0kΩ variable resistor adjusted for a Forward Current (I_F) of 10mA.
- 2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10mA.
- 3. $t_p \gg t_{rr}$

FIGURE 2. FORWARD VOLTAGE

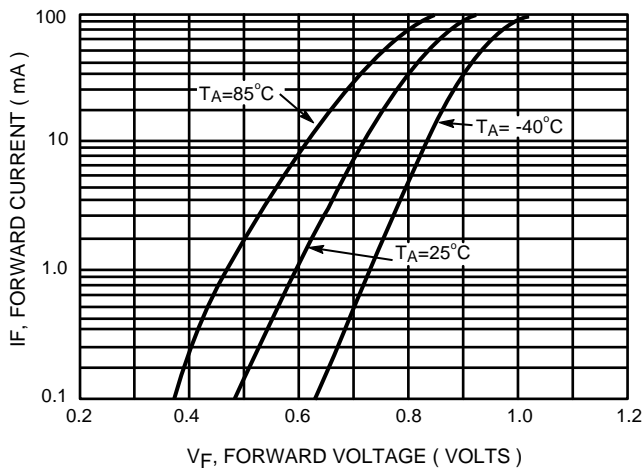


FIGURE 3. LEAKAGE CURRENT

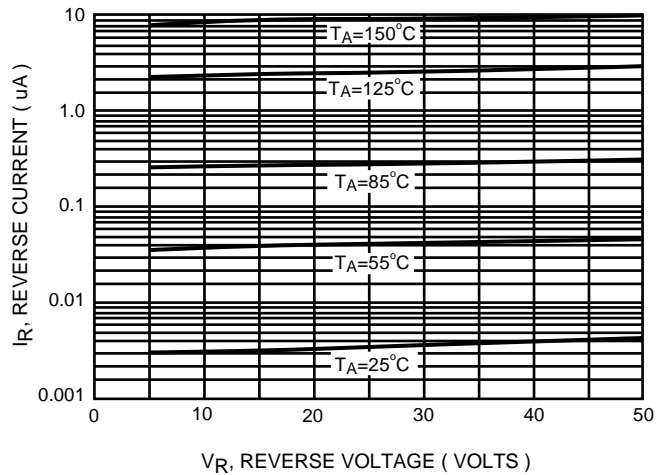


FIGURE 4. CAPACITANCE

